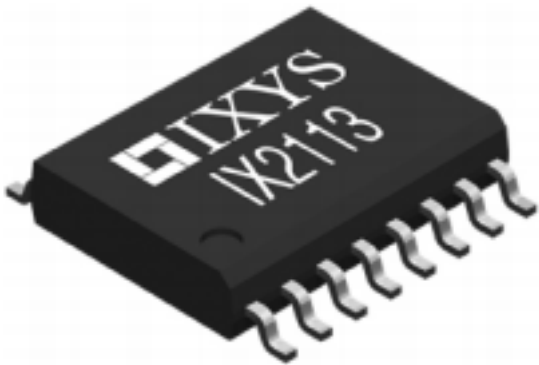


IC drives MOSFETs and IGBTs that operate up to 600V



IXYS Integrated Circuits Division announces the immediate availability of the IX2113 High and Low Side Gate Driver IC. The IX2113 is a high-voltage IC that can drive MOSFETs and IGBTs that operate up to 600V. Both the high-side and low-side outputs feature integrated power DMOS transistors, each capable of sourcing and sinking over 2A of gate-drive current.

High-voltage level shift circuitry allows low voltage logic signals to drive N-channel power MOSFETs and IGBTs in a high-side configuration operating up to 600V. The IX2113's 700V absolute maximum rating provides additional margin for high-voltage applications.

The IX2113 is manufactured on IXYS ICD's advanced HVIC Silicon on Insulator (SOI) process, making the IX2113 very robust in the presence of negative transients, high temperature and high dV/dt noise.

The inputs are 3.3V and 5V logic compatible. Internal under voltage lockout circuitry for both the high-side and low-side outputs does not allow the IX2113 to turn-on the discrete power transistors until there is sufficient gate voltage. The logic supply requires less than 1microA.

The IX2113 can drive power discrete MOSFETs and IGBTs in half-bridge, full-bridge, and 3-phase configurations. Typical applications include motor drives, high voltage inverters, uninterrupted power supplies (UPS), and DC/DC converters. The IX2113 complements IXYS ICD's extensive low side gate driver and optically isolated gate driver portfolios, and the full range of IXYS power semiconductors.

www.ixysic.com [1]

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